# GL05T to GL24T

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**Vishay Semiconductors** 

# Low Capacitance ESD Protection Diodes for **High-Speed Data Interfaces**

**FEATURES** 

SOT-23 package

• e3 - Sn

equipment, peripherals

• AEC-Q101 qualified available

 IEC 61000-4-5 (lightning) see I<sub>PPM</sub> below • ESD immunity acc. IEC 61000-4-2 ± 8 kV contact discharge ± 15 kV air discharge

• ESD capability according to AEC-Q101:

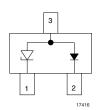
human body model: class H3B: > 8 kV

· Low capacitance for high speed data lines,

please see www.vishay.com/doc?99912

cellular handsets, USB port protection, LAN

· Material categorization: for definitions of compliance





2035

click logo to get started

#### MARKING

(example only)



Bar = cathode marking YYY = type code (see table below)

XX = date code

#### **DESIGN SUPPORT TOOLS**



ORDERING INFORMATION									
	ENVIR	ONMENTAL AN	ID QUALITY CO	ODE	PACKAG	ING CODE			
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS-CON LEAD (PI		EE TIN (8 mm TAPE), (8 mm TAPE),	ORDERING CODE (EXAMPLE)				
(,	QUALIFIED	STANDARD	GREEN	FLATED	15K/BOX = MÓQ	10K/BOX = MÔQ			
GL05T-		E		3	-08		GL05T-E3-08		
GL05T-			G	3	-08		GL05T-G3-08		
GL05T-	Н	E		3	-08		GL05T-HE3-08		
GL05T-	Н		G	3	-08		GL05T-HG3-08		
GL05T-		E		3		-18	GL05T-E3-18		
GL05T-			G	3		-18	GL05T-G3-18		
GL05T-	Н	E		3		-18	GL05T-HE3-18		
GL05T-	Н		G	3		-18	GL05T-HG3-18		

PACK	PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
GL05T	SOT-23	L05	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
GLUUT	GL05T SOT-23 L06 Green 8.1 mg UL 94 V-0		UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C				
GL12T	SOT-23	L12	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
GLIZI	301-23	L13	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
GL15T	SOT-23	L15	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
GLIJI	301-23	L16	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
GL24T	SOT-23	L24	Standard	8.8 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
GL241	501-25	L25	Green	8.1 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		

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Document Number: 85809

RoHS COMPLIANT HALOGEN FREE <u>GREEN</u> (5-2008)



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ABSOLUTE MAXIMU	IM RATINGS GL05	т			
PARAMETER	TEST	CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	8/20 µs	Pin 1-2 (pin 3 n.c.)	I <sub>PPM</sub>	25	А
Peak pulse power	8/20 µs waveform	Fin 1-2 (pin 3 n.c.)	P <sub>PP</sub>	300	W
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	M	± 8	kV
ESD Infinuting	Air discharge acc.	IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV
Blocking voltage	I <sub>B</sub> = 1 μA	Pin 2-1 or pin 2-3	VB	70	V
Operating temperature	Junction temperatu	ire	TJ	-55 to +150	°C
Storage temperature			T <sub>STG</sub>	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS GL12T							
PARAMETER	TEST	TEST CONDITIONS		VALUE	UNIT		
Peak pulse current	8/20 µs	Pin 1-2 (pin 3 n.c.)	I <sub>PPM</sub>	12	А		
Peak pulse power	8/20 µs waveform	Fin 1-2 (pin 3 n.c.)	P <sub>PP</sub>	300	W		
ESD immunity	Contact discharge	acc. IEC 61000-4-2; 10 pulses	M	± 8	kV		
ESD minutity	Air discharge acc. I	EC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV		
Blocking voltage	I <sub>B</sub> = 1 μΑ	Pin 2-1 or pin 2-3	VB	70	V		
Operating temperature	Junction temperatu	ire	TJ	-55 to +150	°C		
Storage temperature			T <sub>STG</sub>	-55 to +150	°C		

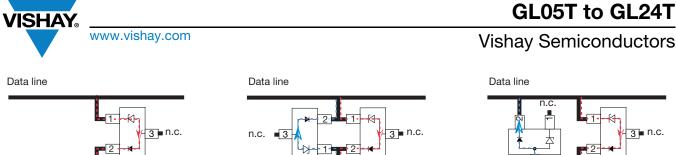
ABSOLUTE MAXIMUM RATINGS GL15T								
PARAMETER	TEST	CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	8/20 µs	Pin 1-2 (pin 3 n.c.)	I <sub>PPM</sub>	10	А			
Peak pulse power	8/20 µs waveform	Fin 1-2 (pin 3 n.c.)	P <sub>PP</sub>	300	W			
ESD immunity	Contact discharge a	acc. IEC 61000-4-2; 10 pulses	M	± 8	kV			
ESD minunity	Air discharge acc. I	EC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV			
Blocking voltage	I <sub>B</sub> = 1 μΑ	Pin 2-1 or pin 2-3	VB	70	V			
Operating temperature	Junction temperatu	re	TJ	-55 to +150	°C			
Storage temperature			T <sub>STG</sub>	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GL24T							
PARAMETER	TEST	TEST CONDITIONS		VALUE	UNIT		
Peak pulse current	8/20 µs	Pin 1-2 (pin 3 n.c.)	I <sub>PPM</sub>	5	А		
Peak pulse power	8/20 µs waveform	Fin 1-2 (pin 3 n.c.)	P <sub>PP</sub>	300	W		
ESD immunity	Contact discharge a	tact discharge acc. IEC 61000-4-2; 10 pulses		± 8	kV		
ESD minuting	Air discharge acc. I	EC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 8 ± 15	kV		
Blocking voltage	I <sub>B</sub> = 1 μΑ	Pin 2-1 or pin 2-3	VB	70	V		
Operating temperature	Junction temperatu	re	TJ	-55 to +150	°C		
Storage temperature			T <sub>STG</sub>	-55 to +150	°C		

The GLxxT contains an avalanche diode (pin 3-1) and a switching diode (pin 3-2). With pin 1 connected to the signal or data line and pin 2 connected to ground both diodes are in series (pin 3 remains unconnected). The big and robust avalanche diode, driven in reverse direction, provides the working range V<sub>RWM</sub> of 5 V, 12 V, 15 V or 24 V. Due to its size the capacitance of the avalanche diode is in the range of typ. 260 pF (GL05T) and 65 pF (GL24T). The small switching diode in series has a low capacitance of just 2.5 pF (typ.). As both diodes are in series (with pin 3 not connected) the total capacitance of both diodes measured between pin 1 and 2 is as low as the capacitance of the switching diode.

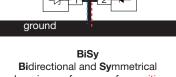
Before the GLxxT can provide this low capacitance the big capacitance of the avalanche diode has to be charged up with the first signal or data pulses. This is usually no problem for digital signals like USB or other data ports.

With the GLxxT a signal or data line can be protected against positive transients only. For negative transients another GLxxT can be used to provide a back path for the negative transients as well.



Uni Unidirectional clamping performance for positive transients only.

ground



clamping performance for positive and negative transients.

# R 3 n.c. grounc

BiAs Bidirectional and Asymmetrical clamping performance for positive and negative transients.

<b>ELECTRICAL CHARACTERISTICS GL05T</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	5	V		
Reverse voltage	at I <sub>R</sub> = 20 μA	V <sub>R</sub>	5	-	-	V		
Reverse current	at V <sub>R</sub> = 5 V	I <sub>R</sub>	-	-	20	μA		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	6.9	7.5	8.0	V		
Boverse elemping veltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	-	9.8	V		
Reverse clamping voltage	at I <sub>PP</sub> = 5 A	VC	-	-	11	V		
Capacitance	at $V_R = 0 V$ ; f = 1 MHz	CD	-	2.5	5	pF		

#### ELECTRICAL CHARACTERISTICS GL12T (T<sub>amb</sub> = 25 °C unless otherwise specified) pin 1 to pin 2: pin 3 not connected

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PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	12	V
Reverse voltage	at I <sub>R</sub> = 1 μA	V <sub>R</sub>	12	-	-	V
Reverse current	at V <sub>R</sub> = 12 V	I <sub>R</sub>	-	-	1	μA
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	13.3	14.3	17.2	V
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V	-	-	19	V
neverse clamping voltage	at I <sub>PP</sub> = 5 A	V <sub>C</sub>	-	-	24	V
Capacitance	at $V_R = 0$ V; f = 1 MHz	CD	-	2.5	5	pF

<b>ELECTRICAL CHARACTERISTICS GL15T</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	15	V		
Reverse voltage	at I <sub>R</sub> = 1 μA	V <sub>R</sub>	15	-	-	V		
Reverse current	at V <sub>R</sub> = 15 V	I <sub>R</sub>	-	-	1	μA		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	16.7	17.7	22	V		
Powerse elemping veltage	at I <sub>PP</sub> = 1 A	V	-	-	24	V		
Reverse clamping voltage	at I <sub>PP</sub> = 5 A	V <sub>C</sub>	-	-	33	V		
Capacitance	at $V_R = 0 V$ ; f = 1 MHz	CD	-	2.5	5	pF		



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<b>ELECTRICAL CHARACTERISTICS GL24T</b> (T <sub>amb</sub> = 25 °C unless otherwise specified) pin 1 to pin 2; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	24	V		
Reverse voltage	at I <sub>R</sub> = 1 μA	V <sub>R</sub>	24	-	-	V		
Reverse current	at V <sub>R</sub> = 24 V	I <sub>R</sub>	-	-	1	μA		
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	26.7	28.2	33	V		
Deverse elementes veltase	at I <sub>PP</sub> = 1 A	V	-	-	43	V		
Reverse clamping voltage	at I <sub>PP</sub> = 5 A	V <sub>C</sub>	-	-	55	V		
Capacitance	at $V_R = 0 V$ ; f = 1 MHz	CD	-	2.5	5	pF		

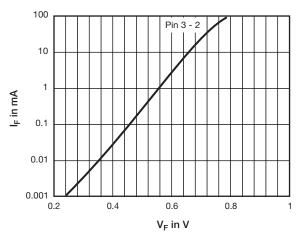


Fig. 1 - Typical Forward Current  $I_{\text{F}}$  vs. Forward Voltage  $V_{\text{F}}$ 

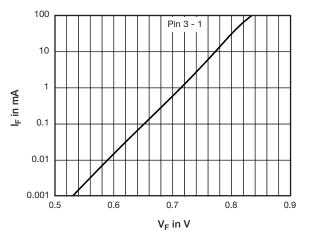


Fig. 2 - Typical Forward Current I<sub>F</sub> vs. Forward Voltage V<sub>F</sub>

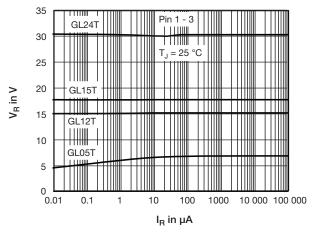


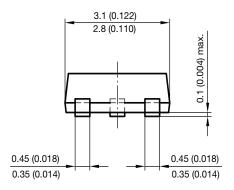
Fig. 3 - Typical Reverse Voltage  $V_{\mathsf{R}}$  vs. Reverse Current  $\mathsf{I}_{\mathsf{R}}$ 

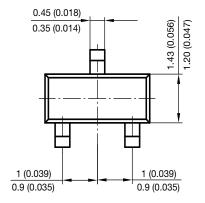
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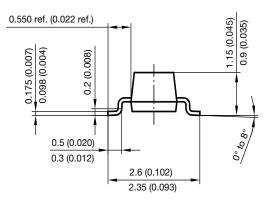


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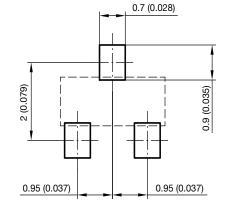
#### PACKAGE DIMENSIONS in millimeters (inches): SOT-23





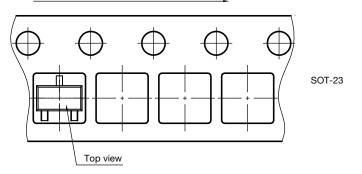


Foot print recommendation:



Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23. Sep. 2009 17418

Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607 Unreeling direction





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